Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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Microsemi LAWRENCE

TECHNICAL DATA

SILICON CONTROLLED RECTIFIER

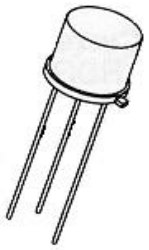
Qualified per MIL-PRF-19500/ 276

Devices					***Qualified Level***
2N2323	**2N2324**	**2N2326**	**2N2328**		**JAN**
2N2323S	**2N2324S**	**2N2326S**	**2N2328S**	**2N2329**	**JANTX**
2N2323A	**2N2324A**	**2N2326A**	**2N2328A**	**2N2329S**	**JANTXV**
2N2323AS	**2N2324AS**	**2N2326AS**	**2N2328AS**		

MAXIMUM RATINGS

Ratings	Sym	2N2323,S/ 2N2323A,S	2N2324,S/ 2N2324A,S	2N2326,S/ 2N2326A,S	2N2328,S/ 2N2328A,S	2N2329,S	Unit
Reverse Voltage	V_{RM}	50	100	200	300	400	Vdc
Working Peak Reverse Voltage	V_{RM}	75	150	300	400	500	Vpk
Forward Blocking Voltage	V_{FBXM}	50(3/4)	100(3/4)	200(3/4)	300(3/4)	400(3)	Vpk
Average Forward Current (1)	I_O	0.22					Adc
Forward Current Surge Peak(2)	I_{FSM}	15					Adc
Cathode-Gate Current	V_{KGM}	6					Vpk
Operating Temperature	T_{op}	-65 to +125					^{0}C
Storage Junction Temp	T_{stg}	-65 to +150					^{0}C

1) This average forward current is for an ambient temperature of 80^{0}C and 180 electrical degrees of conduction.
2) Surge current is non-recurrent. The rate of rise of peak surge current shall not exceed 40 A during the first 5 µs after switching from the 'off' (blocking) to the 'on' (conducting) state. This is measured from the point where the thyristor voltage has decayed to 90% of its initial blocking value.
3) Gate connected to cathode through 1,000 ohm resistor.
4) Gate connected to cathode through 2,000 ohm resistor.



TO-5

*See appendix A for package outline

ELECTRICAL CHARACTERISTICS

Characteristics		Symbol	Min.	Max.	Unit
SUBGROUP 2 TESTING					
Reverse Blocking Current					
R_2 = 1 kµ	2N2323 thru 2N2329				
	2N2323S thru 2N2329S				
R_2 = 2 kµ	2N2323A thru 2N2328A				
	2N2323AS thru 2N2328AS	I_{RBX1}		10	µAdc
V_R = 50 Vdc	2N2323, S, A, AS				
V_R = 100 Vdc	2N2324, S, A, AS				
V_R = 200 Vdc	2N2326, S, A, AS				
V_R = 300 Vdc	2N2328, S, A, AS				
V_R = 400 Vdc	2N2329, S,				

ELECTRICAL CHARACTERISTICS (con't)

Characteristics		Symbol	Min.	Max.	Unit
Forward Blocking Current					
R_2 = 1 kΩ	2N2323 thru 2N2329				
	2N2323S thru 2N2329S				
R_2 = 2 kΩ	2N2323A thru 2N2328A				
	2N2323AS thru 2N2328AS	I_{FBX1}		10	μAdc
V_R = 50 Vdc	2N2323, S, A, AS				
V_R = 100 Vdc	2N2324, S, A, AS				
V_R = 200 Vdc	2N2326, S, A, AS				
V_R = 300 Vdc	2N2328, S, A, AS				
V_R = 400 Vdc	2N2329, S				
Reverse Gate Current					
V_{KG} = 6 Vdc		I_{KG}		200	μAdc
Gate Trigger Voltage and Current					
$V_2 = V_{FBX}$ = 6 Vdc; R_L = 100 Ω					
R_e = 1 kΩ	2N2323 thru 2N2329 and	V_{GT1}	0.35	0.80	Vdc
	2N2323S thru 2N2329S	I_{GT1}		200	μAdc
R_e = 2 kΩ	2N2323A thru 2N2328A and	V_{GT1}	0.35	0.60	Vdc
	2N2323AS thru 2N2328AS	I_{GT1}		20	μAdc

SUBGROUP 4 TESTING

Exponential Rate of Voltage Rise $T_A = 125^0$C					
50 Ω ≤ R_L ≤ 400 Ω, C = 0.1 to 1.0 μF, repetition rate = 60 pps, test duration = 15 seconds					
dv/dt = 1.8 v/μs, R_3 = 1 kΩ	2N2323 thru 2N2329 and 2N2323S thru 2N2329S				
dv/dt = 0.7 v/μs, R_3 = 2 kΩ	2N2323A thru 2N2328A and 2N2323AS thru 2N2328AS	V_{FBX}			Vdc
V_{AA} = 50 Vdc	2N2323, S, A, AS		47		
V_{AA} = 100 Vdc	2N2324, S, A, AS		95		
V_{AA} = 200 Vdc	2N2326, S, A, AS		190		
V_{AA} = 300 Vdc	2N2328, S, A, AS		285		
V_{AA} = 400 Vdc	2N2329, S		380		
Forward "on" Voltage					
i_{FM} = 4a (pk) (pulse), pulse width = 8.5 ms, max; duty cycle = 2% max		V_{FM}		2.2	V(pk)
Holding Current					
V_{AA} = 24 Vdc max, I_{F1} = 100 mAdc, I_{F2} = 10 mAdc					
Gate trigger source voltage = 6 Vdc,					
trigger pulse width = 25 μs min., R_2 = 330 Ω					
R_3 = 1 kΩ	2N2323 thru 2N2329 and 2N2323S thru 2N2329S	I_{HOX}		2.0	mAdc
R_3 = 2 kΩ	2N2323A thru 2N2328A and 2N2323AS thru 2N2328AS				